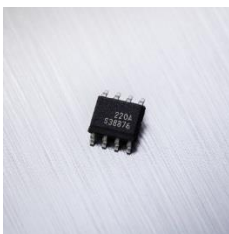


MLX91220 Integrated Current Sensor IC

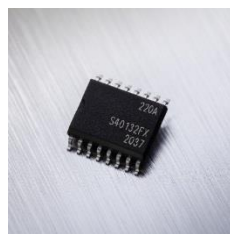
Datasheet

Features and Benefits

- Factory trimmed AC and DC current sensor
- Analog ratiometric or fixed output voltage
- Combining sensing element, signal conditioning & isolation in SOIC package
- No application programming required
- High speed sensing
 - DC to 300kHz bandwidth
 - 2 μ s response time
- Robust against external magnetic fields
- No magnetic hysteresis
- Double overcurrent detection (SOIC-16)
- Low ohmic losses of integrated conductor
 - 0.9m Ω SOIC-8 / 0.75m Ω SOIC-16
- SOIC-8 narrow body and SOIC-16 wide body package, RoHS compliant
- Lead free component, suitable for lead free soldering profile up to 260°C, MSL3
- Rated voltage isolation
 - 2.4kV_{RMS} for SOIC-8
 - 4.8kV_{RMS} for SOIC-16



SOIC-8



SOIC-16



IEC/UL 62368-1:2014
(2nd edition)

Applications

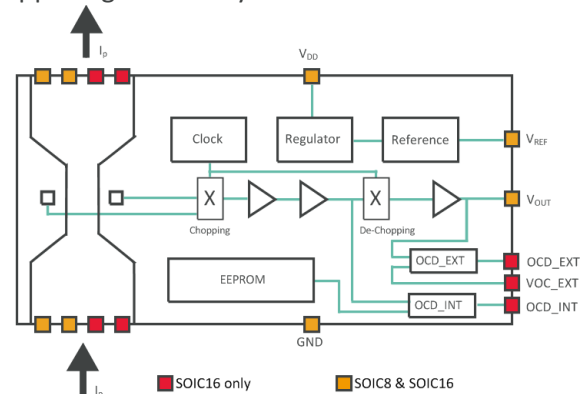
- AC and DC Chargers
- Electric Drives
- DCDC converters
- Solar
- Power Supplies
- Demand/Load control

Description

The MLX91220 is an Isolated Integrated Current Sensor that senses the current flowing through the low impedant leadframe of the SOIC package. By virtue of fixing the current conductor position with respect to the monolithic CMOS sensor, a fully integrated Hall-effect current sensor is obtained, that is factory calibrated.

Inside the package, the magnetic flux density generated by the current flow is sensed differentially by two sets of Hall plates. As a result the influence of external disturbing fields is minimized in the fast analog front-end. The residual signal is amplified to provide a high-speed linear analog output voltage.

The close proximity of the Hall plates to the current conductor ensures a high signal-to-noise ratio and an accurate signal over temperature. Even with this miniaturization, high voltage isolation ratings are still maintained between the primary and the opposing secondary side.



Contents

Features and Benefits.....	1
Applications.....	1
Description.....	1
Contents.....	2
1. Ordering Information	3
2. Functional Diagram	5
3. Glossary of Terms.....	7
4. Pinout.....	8
5. Absolute Maximum Ratings	9
6. MLX91220 General Electrical Specification.....	10
7. MLX91220 General Current Specification	11
8. MLX91220 Voltage Isolation Specification	12
9. MLX91220 Timing Specification.....	13
10. MLX91220 Accuracy Specifications.....	14
10.1. Definitions	14
10.2. MLX91220KDx-ABF-117	16
10.3. MLX91220KDx-ABR-020	17
10.4. MLX91220KDx-ABR-025	18
10.5. MLX91220KDx-ABF-025	19
10.6. MLX91220KDx-ABR-030	20
10.7. MLX91220KDx-ABR-050	21
10.8. MLX91220KDx-ABF-050	22
10.9. MLX91220KDx-ABR-075 Specifications	23
10.10. MLX91220KDx-ABF-075	24
11. MLX91220 Overcurrent Detection.....	25
11.1. General.....	25
11.2. Electrical Specifications	26
11.3. Internal Overcurrent Detection Principle	26
11.4. External Overcurrent Detection Principle	27
12. Recommended Application Diagrams.....	28

12.1. Resistor and Capacitor Values.....	28
12.2. SOIC8 Application Diagram	28
12.3. SOIC16 Application Diagram	29
13. Standard information regarding manufacturability with different soldering processes	30
14. ESD Precautions.....	31
15. Package Information.....	32
15.1. SOIC-8 150mils - Package Dimensions.....	32
15.2. SOIC-16 300mils - Package Dimensions.....	33
16. Disclaimer.....	34

1. Ordering Information

Product Code	Package	Current Measurement Range	Output type	Sensitivity	OCD level
MLX91220KDC-ABF-025-RE	SOIC8	25 A	Fixed	80 mV/A	27.8 A
MLX91220KDC-ABF-050-RE	SOIC8	50 A	Fixed	40 mV/A	55.6 A
MLX91220KDC-ABR-020-RE	SOIC8	20 A	Ratiometric	100 mV/A	22.2 A
MLX91220KDC-ABR-025-RE	SOIC8	25 A	Ratiometric	80 mV/A	27.8 A
MLX91220KDC-ABR-030-RE	SOIC8	30 A	Ratiometric	66 mV/A	33.7 A
MLX91220KDC-ABR-050-RE	SOIC8	50 A	Ratiometric	40 mV/A	55.6 A
MLX91220KDF-ABF-117-RE	SOIC16	17 A	Fixed	120 mV/A	14.8 A
MLX91220KDF-ABF-025-RE	SOIC16	25 A	Fixed	80 mV/A	27.8 A
MLX91220KDF-ABF-050-RE	SOIC16	50 A	Fixed	40 mV/A	55.6 A
MLX91220KDF-ABR-075-RE	SOIC16	75 A	Ratiometric	26.7 mV/A	83.4 A
MLX91220KDF-ABF-075-RE	SOIC16	75 A	Fixed	26.7 mV/A	83.4 A
MLX91220KDF-ABR-025-RE	SOIC16	25 A	Ratiometric	80 mV/A	27.8 A
MLX91220KDF-ABR-050-RE	SOIC16	50 A	Ratiometric	40 mV/A	55.6 A

Legend:

Temperature Code:	K: from -40°C to 125°C ambient temperature
Package Code:	“DC” for SOIC-8 NB (Narrow Body – 150mils) package “DF” for SOIC-16 WB (Wide Body – 300mils) package
Option Code:	Axx-xxx: die version xBx-xxx: “B” for bipolar ⁽¹⁾ and “U” for unipolar xxF-xxx: “F” for fixed mode output and “R” for ratiometric output xxx-0xx: “0” for default trimming xxx-x50: “50” for Full Scale current measurement (corresponding to 2V excursion from V_{OQ} in bipolar case, and 4V excursion in unipolar case)
Packing Form:	“RE” for Reel
Ordering Example:	MLX91220KDC-ABF-050-RE

Table 1 – Legend

- (1) Bipolar output indicates that the sensor provides a symmetrical output around the 0A point which is set at half the output voltage ($50\% V_{DD}$) in case of ratiometric mode, and V_{REF} equals $50\% V_{DD}$ in case of fixed mode. Both designs imply sensing of positive and negative currents.

Melexis is continuously expanding its product portfolio by adding new option codes to better meet the needs of our customer’s applications. This table is being updated frequently, please go to the [Melexis website](#) to download the latest version of this datasheet. For custom transfer characteristics, please contact your local Melexis Sales representative or distributor.

2. Functional Diagram

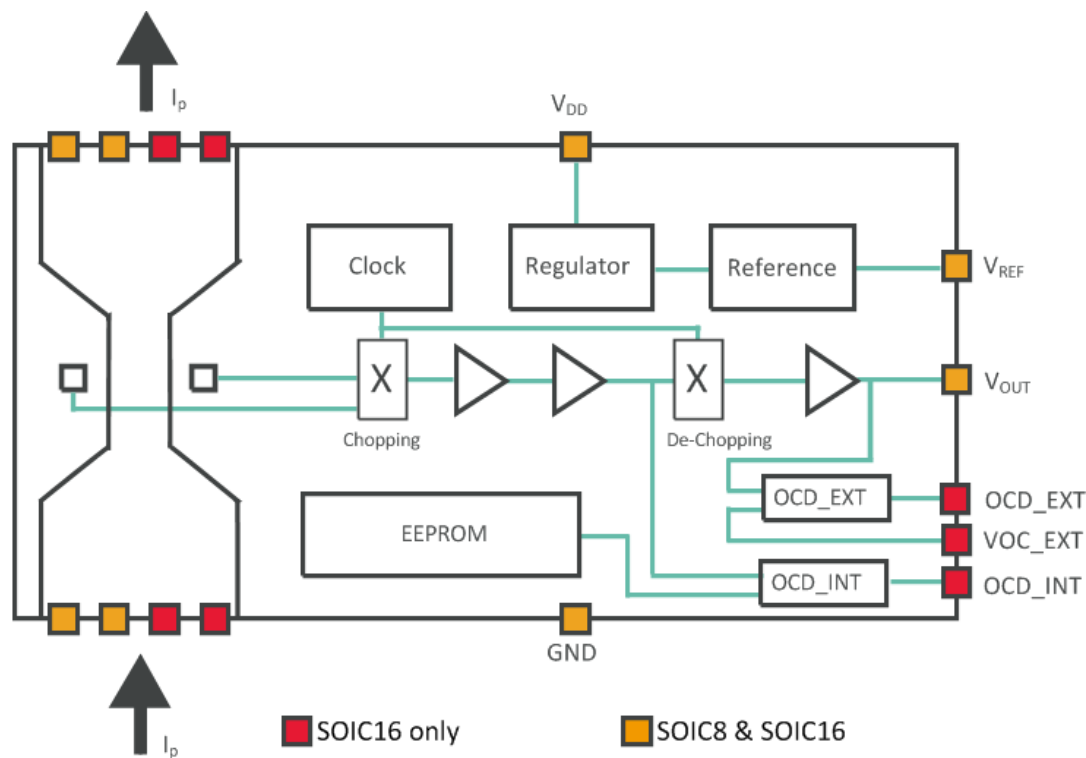
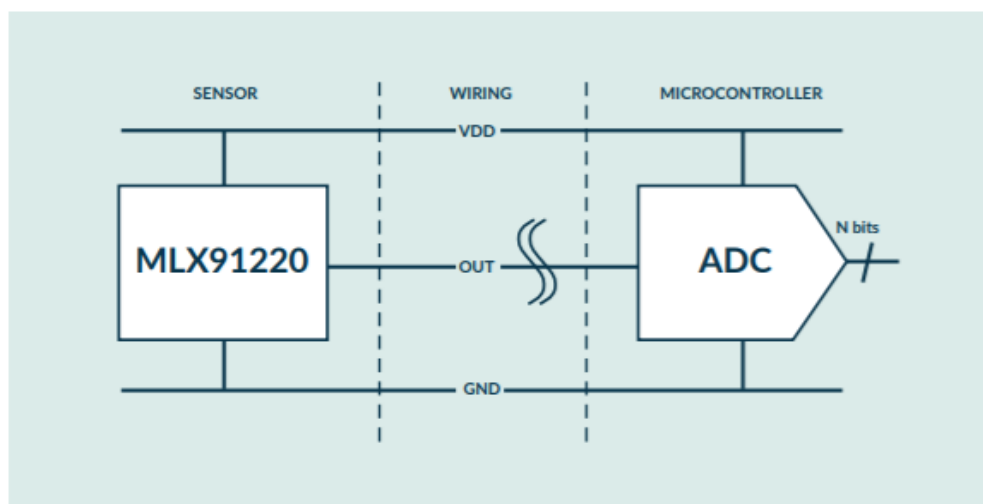


Figure 1: Functional Diagram for MLX91220

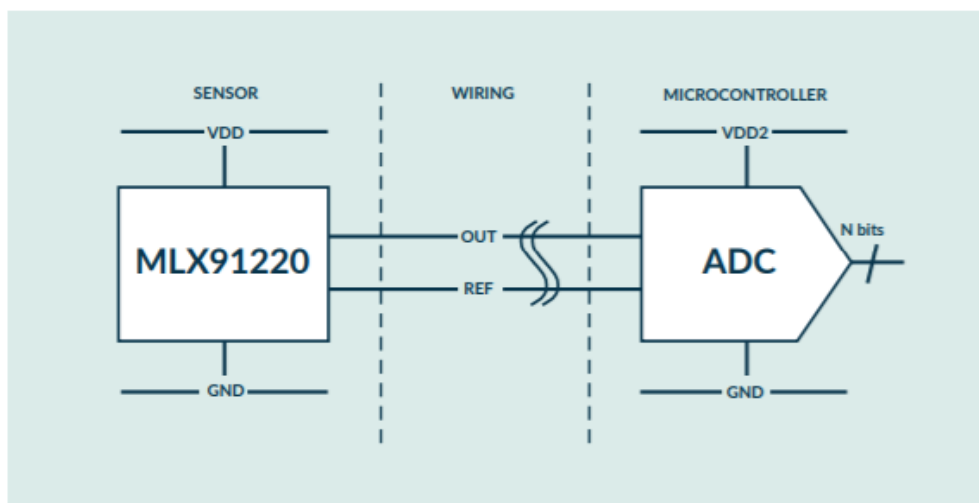
The sensor can be used in 2 different modes, depending on the application. Both modes rely on the output voltage of the sensor being proportional to the flow of current, but the difference resides in the signal reconstruction.

Ratiometric Mode



No matter if the V_{DD} line is at 5V or deviating $\pm 10\%$, the ADC code for a given measured current will always be the same as the ADC is supplied by the same voltage as the sensor. The sensor has a sensitivity expressed in $\%V_{DD}/A$.

Differential or Fixed Mode⁽¹⁾



In this particular case the ADC does not necessarily share the same supply voltage with the sensor. For this reason, the sensor is calibrated with an absolute sensitivity regardless of the actual supply voltage. The output signal can be reconstructed by taking the difference between the output and the reference voltage from the IC. The ADC gets these two signals as inputs for establishing the sensed current accurately, and is not influenced by the supply voltage differences between both sensor and microcontroller, if applicable.

Parameter	Ratiometric Mode	Differential or Fixed Mode
Output Signal	$V_{OUT} [\%V_{DD}]$ Example: output is 2.5V when supply is 5V → output is then 50% V_{DD} . If the supply (V_{DD}) increases with 5% to 5.25V the sensor output will (for the same measured input current) scale proportionally with the supply voltage, becoming 2.625V, but as a percentage (i.e. ratiometrically seen) it remains at 50% of V_{DD} .	$V_{OUT} - V_{REF} [V]$ Example: output is 2.501V and V_{REF} is 2.501V when supply is 5V. When the supply voltage is increasing to 5.1V due to supply system variation, the sensor will still maintain the same “fixed” output values V_{OUT} and V_{REF} .
Offset	$V_{OUT}[0A] = 50 [\%V_{DD}]$ (factory trimmed)	$V_{REF} = 2.5 [V]$ (factory trimmed) $V_{OUT}[0A] - V_{REF} = 0 [V]$
Offset ratiometric	Yes	No
Sensitivity	$[\%V_{DD}/A]$	$[mV/A]$
Sensitivity ratiometric	Yes	No
Measured Current	$(V_{OUT} - V_{OUT}[0A]) / \text{Sensitivity}$	$(V_{OUT} - V_{REF}) / \text{Sensitivity}$

⁽¹⁾ More information can be found in Application Note AN91220_ReferencePin on www.melexis.com

3. Glossary of Terms

Gauss (G), Tesla (T)	Units for the magnetic flux density - 1 mT = 10 G
TC	Temperature Coefficient (in ppm/°C)
NC	Not Connected
IP	Integrated Primary
ASP	Analog Signal Processing
DSP	Digital Signal Processing
AC	Alternate Current
DC	Direct Current
EMC	Electro-Magnetic Compatibility
FS	Full Scale
OCD	OverCurrent Detection

Table 2 – Glossary of Terms

4. Pinout

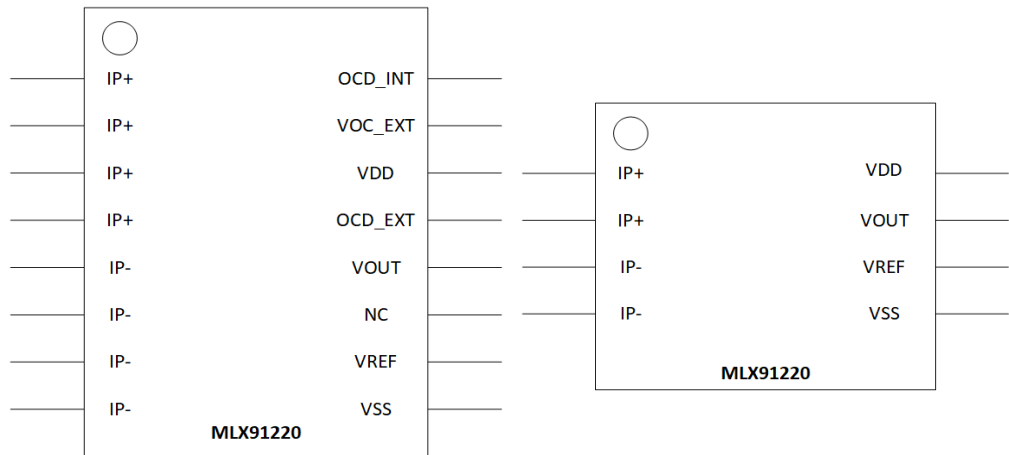


Figure 2 SOIC-16 and SOIC-8 pinouts

PIN	SOIC-8		SOIC-16	
	Pin	Function	Pin	Function
1	IP+	Primary Current Path Input	IP+	Primary Current Path Input
2				
3	IP-	Primary Current Path Output	IP-	Primary Current Path Output
4				
5	V _{SS}	Ground Voltage		
6	V _{REF}	Reference Voltage		
7	V _{OUT}	Output Voltage		
8	V _{DD}	Supply Voltage		
9			V _{SS}	Ground Voltage
10			V _{REF}	Reference Voltage
11			NC	Not connected
12			V _{OUT}	Output Voltage
13			OCD _{EXT}	External OCD
14			V _{DD}	Supply Voltage
15			VOC _{EXT}	External Overcurrent threshold voltage
16			OCD _{INT}	Internal OCD

For optimal EMC behavior, it is recommended to connect the unused pin (NC) to V_{SS} (see Chapter 12).

5. Absolute Maximum Ratings

Exceeding the absolute maximum ratings may cause permanent damage. Exposure to absolute maximum-rated conditions for extended periods may affect device reliability

Parameter	Value
Positive Supply Voltage (overvoltage)	+ 8 V
Positive Supply Voltage (maintaining application mode)	+ 6.5 V
Reverse Supply Voltage	- 0.3 V
Positive Pin Voltage ⁽¹⁾	$V_{DD} + 0.3 \text{ V}$
Output Sourcing Current	+ 25 mA
Reverse Pin Voltage ⁽¹⁾	- 0.3 V
Output Sinking Current	+50 mA
Operating Ambient Temperature Range, T_A	- 40°C to + 125°C
Storage Temperature Range, T_S	- 40°C to + 150°C
Maximum Junction Temperature, T_J ⁽²⁾	+ 165°C

(1) Except for V_{DD} and V_{SS}

(2) For more information on how the junction temperature relates to the applied current and ambient temperature range, please refer to section 7.

6. MLX91220 General Electrical Specification

DC Operating Parameters at $V_{DD} = 5V$ (unless otherwise specified) and for T_A as specified by the Temperature suffix (K).

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Supply Current	I_{DD}	Without R_{LOAD} , in application mode		20	26	mA
V_{OUT} output resistance	R_{OUT}	$V_{OUT} = 50\%V_{DD}$, $I_{LOAD} = 10\text{ mA}$		1	5	Ω
Voltage Reference Output Resistance	R_{REF}	$V_{REF} = 50\%V_{DD}$, $I_{SINK} = 5\text{ mA}$ or $I_{SOURCE} = 0.2\text{ mA}$	120	200	333	Ω
Output Capacitive Load	C_{LOAD}	Output amplifier stability is optimized for this typical value	0	4.7	6	nF
Common Mode Field Sensitivity ⁽¹⁾	CMFS	For SOIC16		0.4		mA/G
		For SOIC8		0.4		mA/G
Output Short Circuit Current	I_{SHORT}	Output shorted to V_{DD} or V_{SS} - Permanent			180	mA
Output Leakage current	I_{LEAK}	High impedance mode, $T_A = 125^\circ\text{C}$ $T_J < 150^\circ\text{C}$		2	20	μA
Output Voltage Linear Swing	V_{OUT_LSW}	$V_{DD} > 4.6\text{ V}$ for Fixed Mode versions	10		90	$\%V_{DD}$

- (1) Common Mode Field Sensitivity expresses the sensor's susceptibility to a homogenously applied field perpendicular to the package surface. The differential measurement cancels out such common mode magnetic fields, but due to the matching between both Hall plate clusters flanking the current conductor, this is not perfect. This parameter expresses the mA output error as a result of such 1 mT applied field. It has to be noted, that magnetic fields generated by nearby conductors are not homogenous but introduce gradients. More information in this regard can be found in Application Note AN91220_ExternalFieldImmunity on www.melexis.com

7. MLX91220 General Current Specification

DC Operating Parameters at $V_{DD} = 5V$ (unless otherwise specified) and for T_A as specified by the Temperature suffix (K).

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Electrical Resistance of the Primary Current Path	R_{IP_SOIC8} R_{IP_SOIC16}	$T_A = 25^\circ C$		0.9 0.75		m Ω m Ω
Measurement Range	IP_{MAX}	Option Code ABx-117 Option Code ABx-025 Option Code ABx-030 Option Code ABx-050 Option Code ABx-075		16.7 25 30 50 75		A A A A A
Nominal Current	IP_{NOM}	Option Code ABx-117 Option Code ABx-025 Option Code ABx-030 Option Code ABx-050 Option Code ABx-075		6.7 10 12 20 30		A A A A A
Linearity Error	NL	Current in range IP_{NOM} , $T_A = 25^\circ C$			± 0.3	%FS
	NL	Current in range IP_{MAX} , $T_A = 25^\circ C$			± 0.6	%FS
Current Capability ⁽¹⁾	IP_{C85_SOIC8}	Continuous, $T_A = -40$ to $85^\circ C$			± 25	A
	IP_{C25_SOIC8}	Continuous, $T_A = 25^\circ C$			± 40	A
	IP_{C85_SOIC16}	Continuous, $T_A = -40$ to $85^\circ C$			± 30	A
	IP_{C25_SOIC16}	Continuous, $T_A = 25^\circ C$			± 45	A

- (1) Current capability based on the reference Melexis PCB made of 2x 105 μm copper layer without any forced air or other form of cooling. Continuous or RMS current ranges in application are typically higher than this. More information can be found in Application Notes AN91220_FuseCurrent Capability and AN91220_ThermalManagement on www.melexis.com.

8. MLX91220 Voltage Isolation Specification

Parameter	Symbol	Test Conditions	Rating	Units
Dielectric Strength Test Voltage ⁽²⁾ ⁽³⁾	V _{ISO_SOIC8}	IEC 62368-1:2014 (second edition)	2400	V _{RMS}
	V _{ISO_SOIC16}		4800	V _{RMS}
Clearance (primary to secondary)	D _{CL_SOIC8}	Shortest distance through air	4	mm
	D _{CL_SOIC16}		8.1	mm
Creepage (primary to secondary)	D _{CR_SOIC8}	Shortest path along body	3.6	mm
	D _{CR_SOIC16}		7.1	mm
Comparative tracking index	CTI		600	
Working Voltage for Basic Isolation ⁽⁴⁾	V _{WV_SOIC8}	IEC 62368-1:2014 (2 nd edition)	500	V _{RMS}
			707	V _{DC}
	V _{WV_SOIC16}	Based on Pollution degree 2, Material Group II	1000	V _{RMS}
			1414	V _{DC}

- (2) Agency type tested, measured between IP (pin 1-4 on SOIC8, pin 1-8 on SOIC16) and Secondary side (pin 5-8 on SOIC8, pin 9-16 on SOIC16).
- (3) Melexis performs routine production-line tests, for all SOIC8 & SOIC16 devices produced.
- (4) Tension de service pour une isolation principale spécifiée pour un Degré de Pollution 2 et un groupe de matériaux II selon la norme IEC/UL-62368-1:2014 (2^{ème} édition)

9. MLX91220 Timing Specification

DC Operating Parameters at $V_{DD} = 5V$ (unless otherwise specified) and for T_A as specified by the Temperature suffix (K).

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Step Response Time	T_{RESP}	Delay between the input signal reaching 90% and the output reaching 90% (see Figure 3)			2	μs
Bandwidth	BW	-3dB, $T_A = 25^\circ C$		300		kHz
Power on Delay ⁽⁵⁾	T_{POD}	V_{REF} capacitor = 47nF			0.6	ms

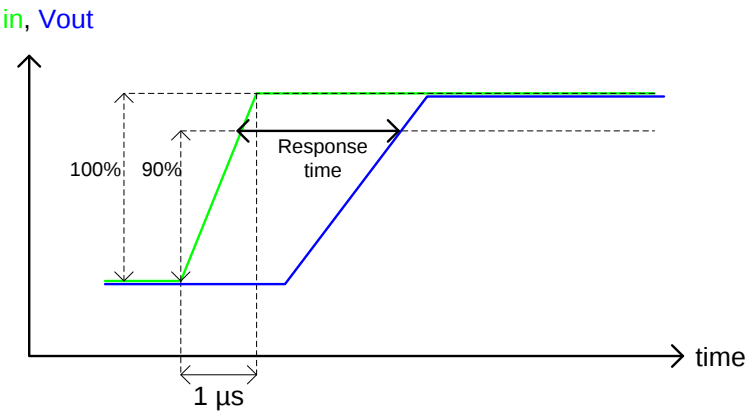


Figure 3: Response Time definition

(5) During the Power-on delay, the output will remain within the 10% fault band at all time.

10. MLX91220 Accuracy Specifications

10.1. Definitions

Thermal Reference Drift

The thermal reference drift is the variation of the reference voltage (V_{REF}) over temperature. It is expressed in ppm/°C.

$$+ \Delta T_{VREF} = \left(\frac{V_{ref}[125^{\circ}\text{C}]}{V_{ref}[35^{\circ}\text{C}]} - 1 \right) \cdot \frac{1}{(125 - 35)} \cdot 10^6$$

$$- \Delta T_{VREF} = \left(\frac{V_{ref}[-40^{\circ}\text{C}]}{V_{ref}[35^{\circ}\text{C}]} - 1 \right) \cdot \frac{1}{(-40 - 35)} \cdot 10^6$$

Voltage Output Quiescent

V_{OQ} corresponds to the output when no current is flowing through the MLX91220 at $T_A=25^{\circ}\text{C}$.

Thermal Offset Drift

ΔT_{VOQ} corresponds to variation of V_{OQ} in temperature.

Sensitivity

The sensitivity is the ratio between the output of the MLX91220 and the input current.

For ratiometric devices, as the output will scale with the supply, sensitivity is expressed as $[\%V_{DD}]/A$.

For fixed devices, the output does not vary with the V_{DD} , sensitivity is thus expressed as mV/A.

Linearity Error

The linearity error is the deviation of the output from the expected linear behaviour. To obtain the linearity error, the current is swept from $-I_{PM}$ to I_{PM} . To decorrelate the thermal drift from the linearity error, the junction temperature should be fixed below 50°C .

$$NL = \frac{V_{out}[I] - BESTFIT(V_{out}[I])}{V_{out}[I_{PM}] - V_{out}[-I_{PM}]} \cdot 100 \text{ } [\%FS]$$

Ratiometry Offset and Sensitivity Error

Ratiometric Mode

In Ratiometric mode, V_{OUT} and V_{REF} are scaled with the supply voltage. $V_{DDnom} = 5V$

Ratiometric V_{OQ} Error:

$$\Delta R_{VOQ} = V_{OQ} [V_{DDnom}] - V_{OQ} [V_{DDnom} \pm 10\%] \cdot \frac{V_{DDnom}}{V_{DDnom} \pm 10\%} \quad [mV]$$

Ratiometric Sensitivity Error:

$$\Delta R_S = 100 \cdot \left(1 - \frac{S[V_{DDnom} \pm 10\%]}{S[V_{DDnom}]} \cdot \frac{V_{DDnom}}{V_{DDnom} \pm 10\%} \right) \quad [\%]$$

Fixed Mode

In Fixed mode, V_{OUT} and V_{REF} are not scaled with the supply voltage. Ideally, they do not vary. $V_{DDnom} = 5V$

Non-Ratiometric V_{OQ} Error:

$$\Delta R_{VOQ} = V_{OQ} [V_{DDnom} \pm 10\%] - V_{OQ} [V_{DDnom}] \quad [mV]$$

Non-Ratiometric Sensitivity Error:

$$\Delta R_S = \left(\frac{S[V_{DDnom} \pm 10\%]}{S[V_{DDnom}]} - 1 \right) \cdot 100 \quad [\%]$$

10.2. MLX91220KDx-ABF-117

DC Operating Parameters at $V_{DD} = 5V$ (unless otherwise specified), for T_A as specified by the Temperature suffix (K) and for $T_J < 150^\circ C$.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Primary current	I_{PM}	For $V_{DD} > 4.6 V$	-16.7		16.7	A
Nominal Supply Voltage	V_{DD}	For I such as $V_{OUT} < V_{DD}-0.1 V$	4.5	5	5.5	V
Voltage Reference	V_{REF}	$T_A=25^\circ C$	2.48	2.5	2.52	V
Thermal Reference Drift	ΔT_{VREF}	Variation versus $25^\circ C$			± 150	ppm/ $^\circ C$
Voltage Output Quiescent	V_{OQ}	No current flowing through IP, $V_{OUT}-V_{REF}$, $T_A=25^\circ C$ No resistive load on V_{OUT} and V_{REF}	-7.5 -63		7.5 63	mV mA
Ratiometry Offset Error	ΔR_{VOQ}	$T_A=25^\circ C$ and for $\pm 10\% V_{DD}$	-5		5	mV
Thermal Offset Drift	ΔT_{VOQ}	Referred to $T_A=25^\circ C$, $IP = 0A$		± 5 ± 42	± 10 ± 84	mV mA
Lifetime Offset Drift	ΔL_{VOQ}			± 2		mV
Sensitivity	S	At $T_A=25^\circ C$ For $T_J < 50^\circ C$	-1 118.8	120	1 121.2	% mV/A
Ratiometry Sensitivity Error	ΔR_S	$T_A=25^\circ C$ and for $\pm 10\% V_{DD}$	-0.6		0.6	%
Thermal Sensitivity Drift	ΔT_S	Current range IP_{MAX}		± 1	± 1.5	%S
Sensitivity Drift over lifetime	ΔL_S			± 1	± 2	%S
Output Noise Spectral Density	N_{SD}	$IP = 0 A$, $T_A=25^\circ C$ within $BW = 1 \dots 100kHz$		179		$\mu A/\sqrt{Hz}$
Output RMS Noise	N_{RMS}	$IP = 0 A$, $T_A=25^\circ C$ $BW = 300kHz$		116		mA_{RMS}
OCD _{INT} Threshold Current ⁽⁶⁾	I_{OCD}			14.8		A
OCD _{INT} Accuracy ⁽⁶⁾	ϵ_{IOCD}	$T_A=25^\circ C$ $T_A=-40^\circ C$ to $85^\circ C$		9.7 17.6		% %
OCD _{EXT} threshold error ⁽⁶⁾	ϵ_{EOCD}		-6		6	%

(6) For SOIC16 version

10.3. MLX91220KDx-ABR-020

DC Operating Parameters at $V_{DD} = 5V$ (unless otherwise specified), for T_A as specified by the Temperature suffix (K) and for $T_j < 150^\circ C$.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Primary current	I_{PM}		-20		20	A
Nominal Supply Voltage	V_{DD}		4.5	5	5.5	V
Thermal Reference Drift	ΔT_{VREF}	Variation versus $25^\circ C$			± 150	ppm/ $^\circ C$
Voltage Output Quiescent	V_{OQ}	No current flowing through IP, $V_{OUT} = -V_{DD}/2$, $T_A = 25^\circ C$ No resistive load on V_{OUT} and V_{REF}	-7.5 -75		7.5 75	mV mA
Ratiometry Offset Error	ΔR_{VOQ}	$T_A = 25^\circ C$ and for $\pm 10\% V_{DD}$	-10		10	mV
Thermal Offset Drift	ΔT_{VOQ}	Referred to $T_A = 25^\circ C$, $I_P = 0A$		± 5 ± 50	± 7.5 ± 75	mV mA
Lifetime Offset Drift	ΔL_{VOQ}			± 2		mV
Sensitivity	S	At $T_A = 25^\circ C$ For $T_j < 50^\circ C$	-1 99	100	1 101	% mV/A
Ratiometry Sensitivity Error	ΔR_S	$T_A = 25^\circ C$ and for $\pm 10\% V_{DD}$		± 0.5		%
Thermal Sensitivity Drift	ΔT_S	Current range $I_{P_{MAX}}$		± 1	± 1.5	%S
Sensitivity Drift over lifetime	ΔL_S			± 1	± 2	%S
Output Noise Spectral Density	N_{SD}	$I_P = 0A$, $T_A = 25^\circ C$ within BW = 1 ... 100kHz		186		$\mu A/\sqrt{Hz}$
Output RMS Noise	N_{RMS}	$I_P = 0A$, $T_A = 25^\circ C$ BW = 300kHz		120		mA_{RMS}
OCD _{INT} Threshold Current ⁽⁷⁾	I_{OCD}			22.2		A
OCD _{INT} Accuracy ⁽⁷⁾	ϵ_{IOCD}	$T_A = 25^\circ C$ $T_A = -40^\circ C$ to $85^\circ C$		8 12		% %
OCD _{EXT} threshold error ⁽⁷⁾	ϵ_{EOCD}		-6		6	%

(7) For SOIC16 version

10.4. MLX91220KDx-ABR-025

DC Operating Parameters at $V_{DD} = 5V$ (unless otherwise specified), for T_A as specified by the Temperature suffix (K) and for $T_J < 150\text{ }^{\circ}\text{C}$.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Primary current	I_{PM}		-25		25	A
Nominal Supply Voltage	V_{DD}		4.5	5	5.5	V
Voltage Output Quiescent	V_{OQ}	No current flowing through IP, $V_{OUT} = V_{DD}/2$, $T_A = 25^{\circ}\text{C}$ No resistive load on V_{OUT} and V_{REF}	-7.5 -94		7.5 94	mV mA
Ratiometry Offset Error	ΔR_{VOQ}	$T_A = 25^{\circ}\text{C}$ and for $\pm 10\% V_{DD}$	-10		10	mV
Thermal Offset Drift	ΔT_{VOQ}	Referred to $T_A = 25^{\circ}\text{C}$, $I_P = 0A$		± 5 ± 63	± 7.5 ± 94	mV mA
Lifetime Offset Drift	ΔL_{VOQ}			± 2		mV
Sensitivity	S	At $T_A = 25^{\circ}\text{C}$ For $T_J < 50\text{ }^{\circ}\text{C}$	-1 79.2	80	1 80.8	% mV/A
Ratiometry Sensitivity Error	ΔR_S	$T_A = 25^{\circ}\text{C}$ and for $\pm 10\% V_{DD}$		± 0.5		%
Thermal Sensitivity Drift	ΔT_S	Current range $I_{P_{MAX}}$		± 1	± 1.5	%S
Lifetime Sensitivity Drift	ΔL_S			± 1	± 2	%S
Output Noise Spectral Density	N_{SD}	$I_P = 0A$, $T_A = 25^{\circ}\text{C}$ within BW = 1 ... 100kHz		190		$\mu\text{A}/\sqrt{\text{Hz}}$
Output RMS Noise	N_{RMS}	$I_P = 0A$, $T_A = 25^{\circ}\text{C}$ BW = 300kHz		129		mA_{RMS}
OCD _{INT} Threshold Current ⁽⁸⁾	I_{OCD}			27.8		A
OCD _{INT} Accuracy ⁽⁸⁾	ϵ_{IOCD}	$T_A = 25^{\circ}\text{C}$ $T_A = -40^{\circ}\text{C}$ to 85°C		7.5 11.5		% %
OCD _{EXT} threshold error ⁽⁸⁾	ϵ_{EOCD}		-6		6	%

(8) For SOIC16 version

10.5. MLX91220KDx-ABF-025

DC Operating Parameters at $V_{DD} = 5V$ (unless otherwise specified), for T_A as specified by the Temperature suffix (K) and for $T_J < 150\text{ }^{\circ}\text{C}$.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Primary current	I_{PM}	For $V_{DD} > 4.6\text{ V}$	-25		25	A
Nominal Supply Voltage	V_{DD}	For I such as $V_{OUT} < V_{DD} - 0.1\text{ V}$	4.5	5	5.5	V
Voltage Reference	V_{REF}	$T_A = 25^{\circ}\text{C}$	2.48	2.5	2.52	V
Thermal Reference Drift	ΔT_{VREF}	Variation versus 25°C			± 150	ppm/ $^{\circ}\text{C}$
Voltage Output Quiescent	V_{OQ}	No current flowing through IP, $V_{OUT} - V_{REF}$, $T_A = 25^{\circ}\text{C}$ No resistive load on V_{OUT} and V_{REF}	-7.5 -94		7.5 94	mV mA
Ratiometry Offset Error	ΔR_{VOQ}	$T_A = 25^{\circ}\text{C}$ and for $\pm 10\% V_{DD}$	-5		5	mV
Thermal Offset Drift	ΔT_{VOQ}	Referred to $T_A = 25^{\circ}\text{C}$, $IP = 0A$		± 5 ± 63	± 7.5 ± 94	mV mA
Lifetime Offset Drift	ΔL_{VOQ}			± 2		mV
Sensitivity	S	At $T_A = 25^{\circ}\text{C}$ For $T_J < 50\text{ }^{\circ}\text{C}$	-1 79.2	80	1 80.8	% mV/A
Ratiometry Sensitivity Error	ΔR_S	$T_A = 25^{\circ}\text{C}$ and for $\pm 10\% V_{DD}$	-0.6		0.6	%
Thermal Sensitivity Drift	ΔT_S	Current range IP_{MAX}		± 1	± 1.5	%S
Lifetime Sensitivity Drift	ΔL_S			± 1	± 2	%S
Output Noise Spectral Density	N_{SD}	$IP = 0\text{ A}$, $T_A = 25^{\circ}\text{C}$ within $BW = 1 \dots 100\text{ kHz}$		190		$\mu\text{A}/\sqrt{\text{Hz}}$
Output RMS Noise	N_{RMS}	$IP = 0\text{ A}$, $T_A = 25^{\circ}\text{C}$ $BW = 300\text{ kHz}$		129		mA_{RMS}
OCD _{INT} Threshold Current ⁽⁹⁾	I_{OCD}			27.8		A
OCD _{INT} Accuracy ⁽⁹⁾	ϵ_{IOCD}	$T_A = 25^{\circ}\text{C}$ $T_A = -40^{\circ}\text{C}$ to 85°C		7.5 11.5		% %
OCD _{EXT} threshold error ⁽⁹⁾	ϵ_{EOCD}		-6		6	%

(9) For SOIC16 version

10.6. MLX91220KDx-ABR-030

DC Operating Parameters at $V_{DD} = 5V$ (unless otherwise specified), for T_A as specified by the Temperature suffix (K) and for $T_J < 150\text{ }^{\circ}\text{C}$.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Primary current	I_{PM}		-30		30	A
Nominal Supply Voltage	V_{DD}		4.5	5	5.5	V
Thermal Reference Drift	ΔT_{VREF}	Variation versus 25°C			±150	ppm/°C
Voltage Output Quiescent	V_{OQ}	No current flowing through IP, $V_{OUT} = -V_{DD}/2$, $T_A = 25^{\circ}\text{C}$ No resistive load on V_{OUT} and V_{REF}	-7.5 -112		7.5 112	mV mA
Ratiometry Offset Error	ΔR_{VOQ}	$T_A = 25^{\circ}\text{C}$ and for $\pm 10\% V_{DD}$	-10		10	mV
Thermal Offset Drift	ΔT_{VOQ}	Referred to $T_A = 25^{\circ}\text{C}$, $I_P = 0A$		±5 ±75	±7.5 ±112	mV mA
Lifetime Offset Drift	ΔL_{VOQ}			±2		mV
Sensitivity	S	At $T_A = 25^{\circ}\text{C}$ For $T_J < 50\text{ }^{\circ}\text{C}$	-1 66.0	66.7	1 67.4	% mV/A
Ratiometry Sensitivity Error	ΔR_S	$T_A = 25^{\circ}\text{C}$ and for $\pm 10\% V_{DD}$		±0.5		%
Thermal Sensitivity Drift	ΔT_S	Current range $I_{P_{MAX}}$		±1	±1.5	%S
Lifetime Sensitivity Drift	ΔL_S			±1	±2	%S
Output Noise Spectral Density	N_{SD}	$I_P = 0A$, $T_A = 25^{\circ}\text{C}$ within BW = 1 ... 100kHz		197		μA/√Hz
Output RMS Noise	N_{RMS}	$I_P = 0A$, $T_A = 25^{\circ}\text{C}$ BW = 300kHz		131		mA _{RMS}
OCD _{INT} Threshold Current ⁽¹⁰⁾	I_{OCD}			33.7		A
OCD _{INT} Accuracy ⁽¹⁰⁾	ϵ_{IOCD}	$T_A = 25^{\circ}\text{C}$ $T_A = -40^{\circ}\text{C}$ to 85°C		7 11		% %
OCD _{EXT} threshold error ⁽¹⁰⁾	ϵ_{EOCD}		-6		6	%

⁽¹⁰⁾ For SOIC16 version

10.7. MLX91220KDx-ABR-050

DC Operating Parameters at $V_{DD} = 5V$ (unless otherwise specified), for T_A as specified by the Temperature suffix (K) and for $T_J < 150\text{ }^{\circ}\text{C}$.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Primary current	I_{PM}		-50		50	A
Nominal Supply Voltage	V_{DD}		4.5	5	5.5	V
Thermal Reference Drift	ΔT_{VREF}	Variation versus 25°C			±150	ppm/°C
Voltage Output Quiescent	V_{OQ}	No current flowing through IP, $V_{OUT} = -V_{DD}/2$, $T_A = 25^{\circ}\text{C}$ No resistive load on V_{OUT} and V_{REF}	-7.5 -188		7.5 188	mV mA
Ratiometry Offset Error	ΔR_{VOQ}	$T_A = 25^{\circ}\text{C}$ and for $\pm 10\% V_{DD}$	-10		10	mV
Thermal Offset Drift	ΔT_{VOQ}	Referred to $T_A = 25^{\circ}\text{C}$, $IP = 0A$		±5 ±125	±7.5 ±188	mV mA
Lifetime Offset Drift	ΔL_{VOQ}			±2		mV
Sensitivity	S	At $T_A = 25^{\circ}\text{C}$ For $T_J < 50\text{ }^{\circ}\text{C}$	-1 39.6	40	1 40.4	% mV/A
Ratiometry Sensitivity Error	ΔR_S	$T_A = 25^{\circ}\text{C}$ and for $\pm 10\% V_{DD}$		±0.5		%
Thermal Sensitivity Drift	ΔT_S	Current range IP_{MAX}		±1	±1.5	%S
Lifetime Sensitivity Drift	ΔL_S			±1	±2	%S
Output Noise Spectral Density	N_{SD}	$IP = 0A$, $T_A = 25^{\circ}\text{C}$ within $BW = 1 \dots 100\text{kHz}$		186		μA/√Hz
Output RMS Noise	N_{RMS}	$IP = 0A$, $T_A = 25^{\circ}\text{C}$ $BW = 300\text{kHz}$		126		mA _{RMS}
OCD _{INT} Threshold Current ⁽¹¹⁾	I_{OCD}			55.6		A
OCD _{INT} Accuracy ⁽¹¹⁾	ϵ_{IOCD}	$T_A = 25^{\circ}\text{C}$ $T_A = -40^{\circ}\text{C}$ to 85°C		4.2 6.2		% %
OCD _{EXT} threshold error ⁽¹¹⁾	ϵ_{EOCD}		-6		6	%

⁽¹¹⁾ For SOIC16 version

10.8. MLX91220KDx-ABF-050

DC Operating Parameters at $V_{DD} = 5V$ (unless otherwise specified), for T_A as specified by the Temperature suffix (K) and for $T_J < 150\text{ }^{\circ}\text{C}$.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Primary current	I_{PM}	For $V_{DD} > 4.6\text{ V}$	-50		50	A
Nominal Supply Voltage	V_{DD}	For I such as $V_{OUT} < V_{DD}-0.1\text{ V}$	4.5	5	5.5	V
Voltage Reference	V_{REF}	$T_A=25^{\circ}\text{C}$	2.48	2.5	2.52	V
Thermal Reference Drift	ΔT_{VREF}	Variation versus 25°C			± 150	ppm/ $^{\circ}\text{C}$
Voltage Output Quiescent	V_{OQ}	No current flowing through IP, $V_{OUT}-V_{REF}$, $T_A=25^{\circ}\text{C}$ No resistive load on V_{OUT} and V_{REF}	-7.5 -188		7.5 188	mV mA
Ratiometry Offset Error	ΔR_{VOQ}	$T_A=25^{\circ}\text{C}$ and for $\pm 10\% V_{DD}$	-5		5	mV
Thermal Offset Drift	ΔT_{VOQ}	Referred to $T_A=25^{\circ}\text{C}$, $IP = 0A$		± 5 ± 125	± 7.5 ± 188	mV mA
Lifetime Offset Drift	ΔL_{VOQ}			± 2		mV
Sensitivity	S	At $T_A=25^{\circ}\text{C}$ For $T_J < 50\text{ }^{\circ}\text{C}$	-1 39.6	40	1 40.4	% mV/A
Ratiometry Sensitivity Error	ΔR_S	$T_A=25^{\circ}\text{C}$ and for $\pm 10\% V_{DD}$	-0.6		0.6	%
Thermal Sensitivity Drift	ΔT_S	Current range IP_{MAX}		± 1	± 1.5	%S
Lifetime Sensitivity Drift	ΔL_S			± 1	± 2	%S
Output Noise Spectral Density	N_{SD}	$IP = 0\text{ A}$, $T_A=25^{\circ}\text{C}$ within $BW = 1 \dots 100\text{ kHz}$		186		$\mu\text{A}/\sqrt{\text{Hz}}$
Output RMS Noise	N_{RMS}	$IP = 0\text{ A}$, $T_A=25^{\circ}\text{C}$ $BW = 300\text{ kHz}$		126		mA_{RMS}
OCD _{INT} Threshold Current ⁽¹²⁾	I_{OCD}			55.6		A
OCD _{INT} Accuracy ⁽¹²⁾	ϵ_{IOCD}	$T_A=25^{\circ}\text{C}$ $T_A=-40^{\circ}\text{C}$ to 85°C		4.2 6.2		% %
OCD _{EXT} threshold error ⁽¹²⁾	ϵ_{EOCD}		-6		6	%

⁽¹²⁾ For SOIC16 version

10.9. MLX91220KDx-ABR-075 Specifications

DC Operating Parameters at $V_{DD} = 5V$ (unless otherwise specified), for T_A as specified by the Temperature suffix (K) and for $T_j < 150\text{ }^{\circ}\text{C}$.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Primary current	I_{PM}		-75		75	A
Nominal Supply Voltage	V_{DD}		4.5	5	5.5	V
Thermal Reference Drift	ΔT_{VREF}	Variation versus 25°C			± 150	ppm/ $^{\circ}\text{C}$
Voltage Output Quiescent	V_{OQ}	No current flowing through IP, $V_{OUT} = -V_{DD}/2$, $T_A = 25^{\circ}\text{C}$ No resistive load on V_{OUT} and V_{REF}	-7.5 -281		7.5 281	mV mA
Ratiometry Offset Error	ΔR_{VOQ}	$T_A = 25^{\circ}\text{C}$ and for $\pm 10\% V_{DD}$	-10		10	mV
Thermal Offset Drift	ΔT_{VOQ}	Referred to $T_A = 25^{\circ}\text{C}$, $I_P = 0A$		± 5 ± 187	± 7.5 ± 281	mV mA
Lifetime Offset Drift	ΔL_{VOQ}			± 2		mV
Sensitivity	S	At $T_A = 25^{\circ}\text{C}$ For $T_j < 50\text{ }^{\circ}\text{C}$	-1 26.4	26.7	1 27	% mV/A
Ratiometry Sensitivity Error	ΔR_S	$T_A = 25^{\circ}\text{C}$ and for $\pm 10\% V_{DD}$		± 0.5		%
Thermal Sensitivity Drift	ΔT_S	Current range $I_{P_{MAX}}$		± 1	± 1.5	%S
Sensitivity Drift over lifetime	ΔL_S			± 1	± 2	%S
Output Noise Spectral Density	N_{SD}	$I_P = 0A$, $T_A = 25^{\circ}\text{C}$ within BW = 1 ... 100kHz		207		$\mu\text{A}/\sqrt{\text{Hz}}$
Output RMS Noise	N_{RMS}	$I_P = 0A$, $T_A = 25^{\circ}\text{C}$ BW = 300kHz		143		mA_{RMS}
OCD _{INT} Threshold Current ⁰	I_{OCD}			83.4		A
OCD _{INT} Accuracy ⁰	ϵ_{IOCD}	$T_A = 25^{\circ}\text{C}$ $T_A = -40^{\circ}\text{C}$ to 85°C		4 6		% %
OCD _{EXT} threshold error ⁽¹³⁾	ϵ_{EOCD}		-6		6	%

(13) For SOIC16 version

10.10. MLX91220K Dx-ABF-075

DC Operating Parameters at $V_{DD} = 5V$ (unless otherwise specified), for T_A as specified by the Temperature suffix (K) and for $T_J < 150\text{ }^{\circ}\text{C}$.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Primary current	I_{PM}	For $V_{DD} > 4.6\text{ V}$	-75		75	A
Nominal Supply Voltage	V_{DD}	For I such as $V_{OUT} < V_{DD}-0.1\text{ V}$	4.5	5	5.5	V
Voltage Reference	V_{REF}	$T_A=25^{\circ}\text{C}$	2.48	2.5	2.52	V
Thermal Reference Drift	ΔT_{VREF}	Variation versus 25°C			± 150	ppm/ $^{\circ}\text{C}$
Voltage Output Quiescent	V_{OQ}	No current flowing through IP, $V_{OUT}-V_{REF}$, $T_A=25^{\circ}\text{C}$ No resistive load on V_{OUT} and V_{REF}	-7.5 -281		7.5 281	mV mA
Ratiometry Offset Error	ΔR_{VOQ}	$T_A=25^{\circ}\text{C}$ and for $\pm 10\% V_{DD}$	-5		5	mV
Thermal Offset Drift	ΔT_{VOQ}	Referred to $T_A=25^{\circ}\text{C}$, IP = 0A		± 5 ± 187	± 7.5 ± 281	mV mA
Lifetime Offset Drift	ΔL_{VOQ}			± 2		mV
Sensitivity	S	At $T_A=25^{\circ}\text{C}$ For $T_J < 50\text{ }^{\circ}\text{C}$	-1 26.4	26.7	1 27	% mV/A
Ratiometry Sensitivity Error	ΔR_S	$T_A=25^{\circ}\text{C}$ and for $\pm 10\% V_{DD}$	-0.6		0.6	%
Thermal Sensitivity Drift	ΔT_S	Current range IP_{MAX}		± 1	± 1.5	%S
Lifetime Sensitivity Drift	ΔL_S			± 1	± 2	%S
Output Noise Spectral Density	N_{SD}	IP = 0 A, $T_A=25^{\circ}\text{C}$ within BW = 1 ... 100kHz		207		$\mu\text{A}/\sqrt{\text{Hz}}$
Output RMS Noise	N_{RMS}	IP = 0 A, $T_A=25^{\circ}\text{C}$ BW = 300kHz		143		mA_{RMS}
OCD _{INT} Threshold Current ⁰	I_{OCD}			83.4		A
OCD _{INT} Accuracy ⁰	ϵ_{IOCD}	$T_A=25^{\circ}\text{C}$ $T_A=-40^{\circ}\text{C}$ to 85°C		4 6		% %
OCD _{EXT} threshold error ⁰	ϵ_{EOCD}		-6		6	%

(14) For SOIC16 version

11. MLX91220 Overcurrent Detection¹

11.1. General

The MLX91220 provides two OCD features that allow detecting overcurrent applied on the integrated sensor primary. In case of OCD detection, the OCD_{INT} or OCD_{EXT} is pulled to ground. During normal operation the OCD voltage remains at V_{DD}. This OCD feature is available for SOIC16 version only.

The two OCD functions are able to react to an overcurrent event within few us of response time. To avoid false alarm, the overcurrent has to be maintained at least 1μs for the detection to occur. After detection by the sensor the output flag is maintained for 10μs of dwell time. This allows the overcurrent to be easily detected at microcontroller level.

The following table offers a comparison between OCD_{INT} and OCD_{EXT}:

	OCD _{INT}		OCD _{EXT}	
	Min	Max	Min	Max
Typical Application	Short-circuit detection		Out-of-range detection	
Overcurrent effect	OCD _{INT} pin to V _{SS}		OCD _{EXT} pin to V _{SS}	
Detection mode	Bidirectional		Unidirectional / bidirectional	
Accuracy	Lower		Higher	
Threshold trimming	EEPROM		Voltage divider on VOC _{EXT}	
Response time	1.4μs	2.1μs	10μs typical	
Required Input holding time	1μs		10μs minimum	
OCD output dwell time	7 μs	14 μs	10μs typical	

Table 1: Comparison between OCD_{INT} and OCD_{EXT} performances

¹ More information can be found in Application Note AN91220_OverCurrentDetection on www.melexis.com.

11.2. Electrical Specifications

DC Operating Parameters at $V_{DD} = 5V$ (unless otherwise specified) and for T_A as specified by the Temperature suffix (K).

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
OCD_INT Internal ON Resistance	$R_{ON_OCD_INT}$	$I_{SINK} = 1\text{ mA}$	60	90	150	Ω
OCD_EXT Internal ON Resistance	$R_{ON_OCD_EXT}$	$I_{SINK} = 1\text{ mA}$	160	190	280	Ω
VOC_EXT Voltage Range	VOC_EXT		0.3		2	V

11.3. Internal Overcurrent Detection Principle

The internal OCD takes fixed threshold voltage values predefined in the EEPROM and do not require any extra components. The OCD_{INT} implementation allows detecting overcurrent outside of the output measurement range of the sensor and is therefore suitable for large current peaks as occurring during short-circuit. If the theoretical sensor output overcomes the OCD_{INT} voltage threshold, the overcurrent event is flagged on OCD_{INT} pin. The default OCD threshold voltages are defined as follow, but other values can be set on request. The overcurrent threshold in ampere is deduced from the sensitivity of the sensor [mV/A] and the OCD_{INT} threshold voltage.

	Sensor configuration	Min.	Max.
OCD _{INT} Threshold [% FS]	$V_{DD} = 5V / V_{REF} = 2.5V$	27.2	230
	$V_{DD} = 5V / V_{REF} = 0.5V$	13.6	288

Table 2: OCD_{INT} factory programmable range

Sensor reference	Sensitivity [mV/A]	OCD _{INT} Threshold Current [% FS]	OCD _{INT} Threshold Current [A]
MLX91220KDF-ABF-117	120	87.1	14.8
MLX91220KDF-ABx-020	100	111.2	22.2
MLX91220KDx-ABx-025	80	111.2	27.8
MLX91220KDx-ABx-050	40	111.2	55.6

MLX91220KDC-ABR-030	66	112.3	33.7
MLX91220KDF-ABF-075	26.7	111.2	83.4

Table 3: OCD_{INT} threshold currents for SOIC-16 versions

11.4. External Overcurrent Detection Principle

The external OCD uses the voltage applied on VOC_{EXT} pin as threshold voltage. This translates into an overcurrent threshold in ampere depending on the sensitivity of the sensor. A voltage divider on VOC_{EXT} allows defining the threshold voltage in a custom way. Depending on the voltage divider configuration, the OCD_{EXT} can be used either in bidirectional or unidirectional mode. The External OCD threshold is defined within the measurement range of the sensor output. This feature is then suitable for out-of-range detection where the OCD threshold remains close to the nominal current. It offers a better accuracy than OCD_{INT} but the response is slower. The below table presents the unidirectional and bidirectional external OCD configurations. Please refer to section 13.1 and 13.3 for more details about the application diagram and the recommended resistances.

Bidirectional configuration	Unidirectional configuration
$VOC_{EXT} = V_{REF} * \frac{R_{ext_{bi}}}{R_{ext} + R_{ext_{bi}}}$ $VLocd = VOC_{EXT}$ $VHocd = 2 * V_{REF} - VLocd$	$VOC_{EXT} = V_{REF} + (V_{DD} - V_{REF}) * \frac{R_{ext}}{R_{ext} + R_{ext_{uni}}}$ $VHocd = VOC_{EXT}$

Table 4: External OCD, bidirectionnal and unidirectional configurations

12. Recommended Application Diagrams

12.1. Resistor and Capacitor Values

Part	Description	Value	Unit
C ₁	Supply capacitor, EMI, ESD	47	nF
C ₂	Decoupling, EMI, ESD	47	nF
C ₃	Decoupling, EMI, ESD	4.7	nF
$R_{EXT} + R_{EXT_BI} / R_{EXT_UNI}$	External OCD Resistor	$\sim 200^1$	k Ω
R_{EXT_BI} or R_{EXT_UNI}	External OCD Resistor	custom	-

Table 5: Resistor and Capacitor Values for Recommended Application Diagrams

¹ High impedance needed due to the current source/sink limitation of the Vref pin.

12.2. SOIC8 Application Diagram

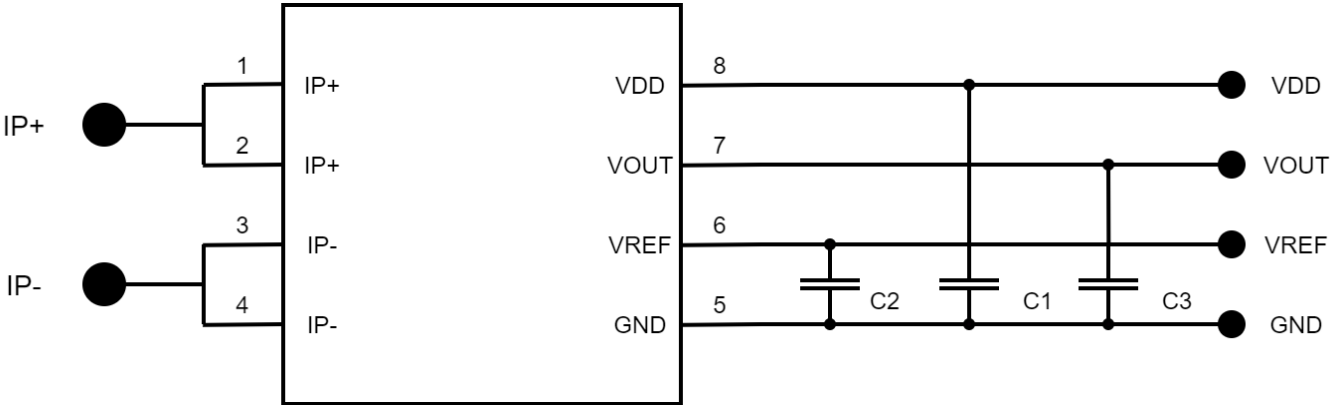


Figure 4: Recommended wiring for the MLX91220 in SOIC-8 package

12.3. SOIC16 Application Diagram

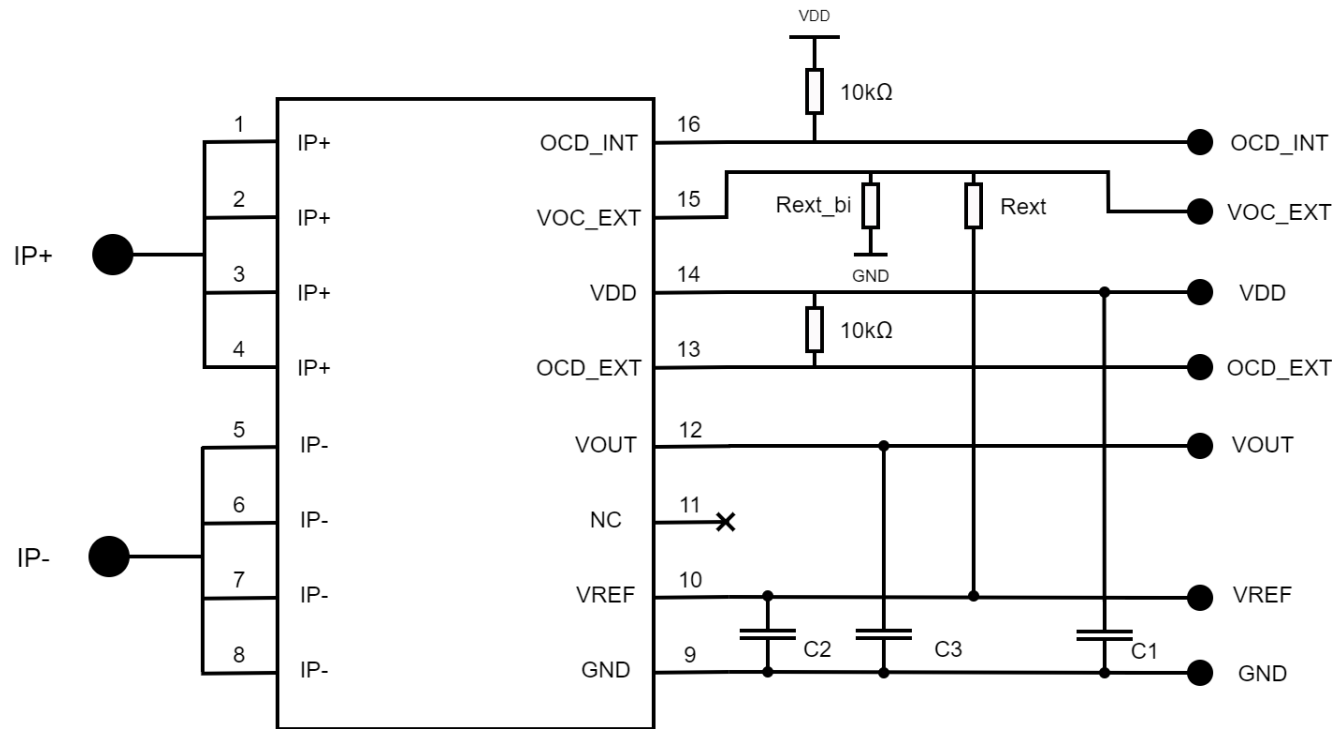


Figure 5: Recommended wiring for the MLX91220 with Bidirectional External OCD

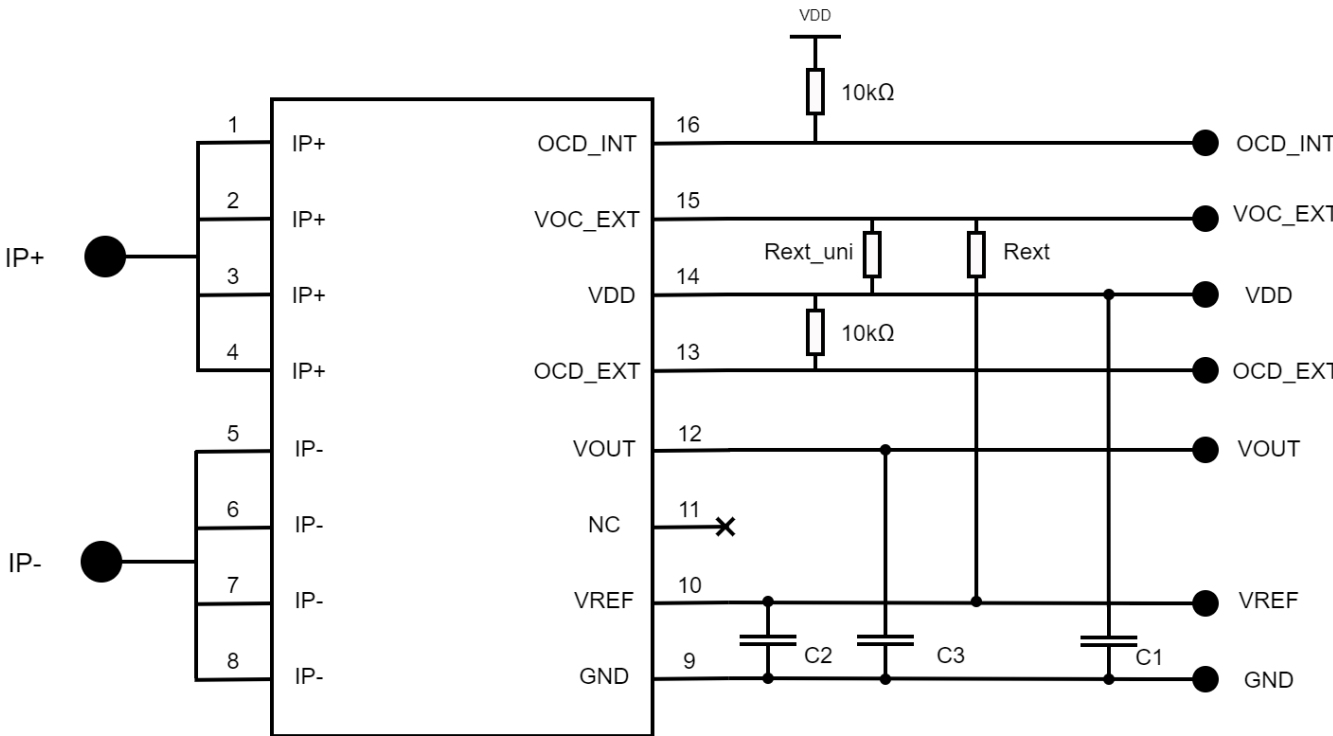


Figure 7: Recommended wiring for the MLX91220 with Unidirectional External OCD

13. Standard information regarding manufacturability with different soldering processes

Our products are classified and qualified regarding soldering technology, solderability and moisture sensitivity level according to following test methods:

Reflow Soldering SMD's (Surface Mount Devices)

- IPC/JEDEC J-STD-020
Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices (classification reflow profiles according to table 5-2)
- EIA/JEDEC JESD22-A113
Preconditioning of Nonhermetic Surface Mount Devices Prior to Reliability Testing (reflow profiles according to table 2)

Wave Soldering SMD's (Surface Mount Devices) and THD's (Through Hole Devices)

- EN60749-20
Resistance of plastic- encapsulated SMD's to combined effect of moisture and soldering heat
- EIA/JEDEC JESD22-B106 and EN60749-15
Resistance to soldering temperature for through-hole mounted devices

Iron Soldering THD's (Through Hole Devices)

- EN60749-15
Resistance to soldering temperature for through-hole mounted devices

Solderability SMD's (Surface Mount Devices) and THD's (Through Hole Devices)

- EIA/JEDEC JESD22-B102 and EN60749-21
Solderability

For all soldering technologies deviating from above mentioned standard conditions (regarding peak temperature, temperature gradient, temperature profile etc) additional classification and qualification tests have to be agreed upon with Melexis.

The application of Wave Soldering for SMD's is allowed only after consulting Melexis regarding assurance of adhesive strength between device and board.

Melexis recommends reviewing on our web site the General Guidelines soldering recommendation (<https://www.melexis.com/en/quality-environment/soldering>).

Melexis is contributing to global environmental conservation by promoting **lead free** solutions. For more information on qualifications of **RoHS** compliant products (RoHS = European directive on the Restriction Of the use of certain Hazardous Substances) please visit the quality page on our website (<https://www.melexis.com/en/quality-environment>).

14. ESD Precautions

Electronic semiconductor products are sensitive to Electro Static Discharge (ESD).

Always observe Electro Static Discharge control procedures whenever handling semiconductor products.



Parameter	Symbol	Test Method	Value	Unit
Human Body ESD Protection	ESD _{HBM}	AEC-Q100-002 Rev D	2	kV
Charged Device Model ESD Protection	ESD _{CDM}	AEC-Q100-011 Rev B	500	V

Table 6: Electrostatic Discharge Ratings

15. Package Information

15.1. SOIC-8 150mils- Package Dimensions

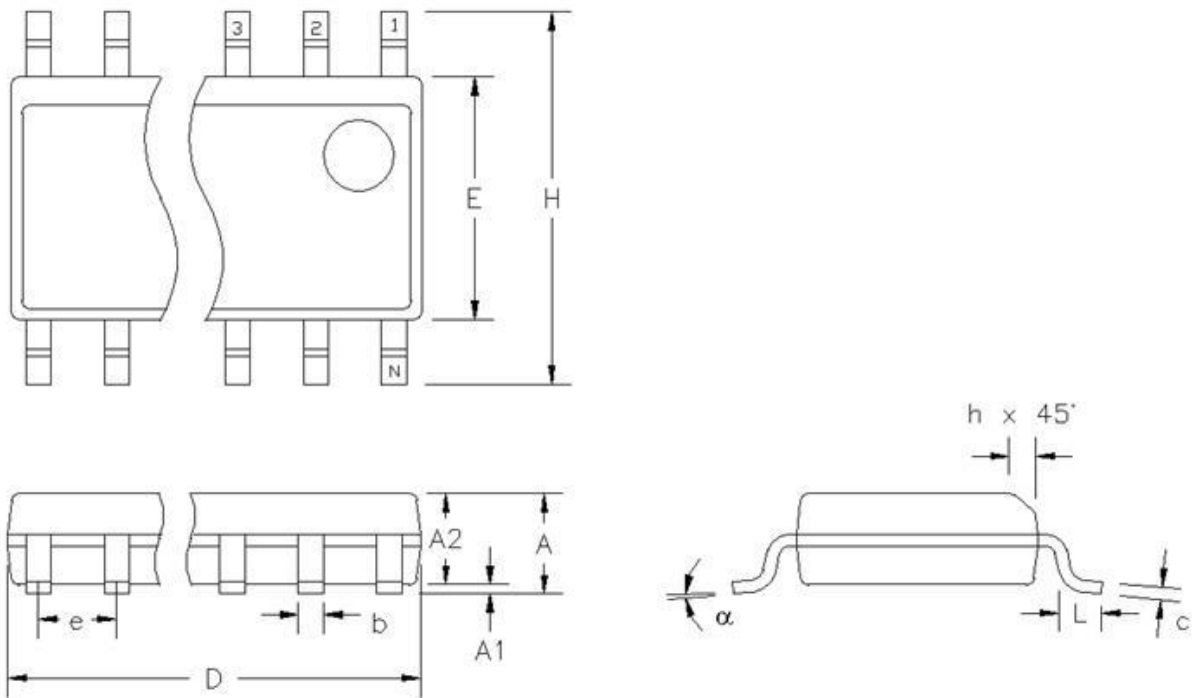


Figure 6 : SOIC8 Package Dimensions [inches]

[mm]	A	A1	A2	D	E	H	L	b	c	e	h	?
min	1.52	0.10	1.37	4.80	3.81	5.80	0.41	0.35	0.19	1.27	0.25	0°
max	1.73	0.25	1.57	4.98	3.99	6.20	1.27	0.49	0.25	BSC	0.50	8°

[inch]	A	A1	A2	D	E	H	L	b	c	e	h	?
min	.060	.004	.054	.189	.150	.228	.016	.014	.008	.050	.010	0°
max	.068	.010	.062	.196	.157	.244	.050	.019	.010	BSC	.020	8°

15.2. SOIC-16 300mils- Package Dimensions

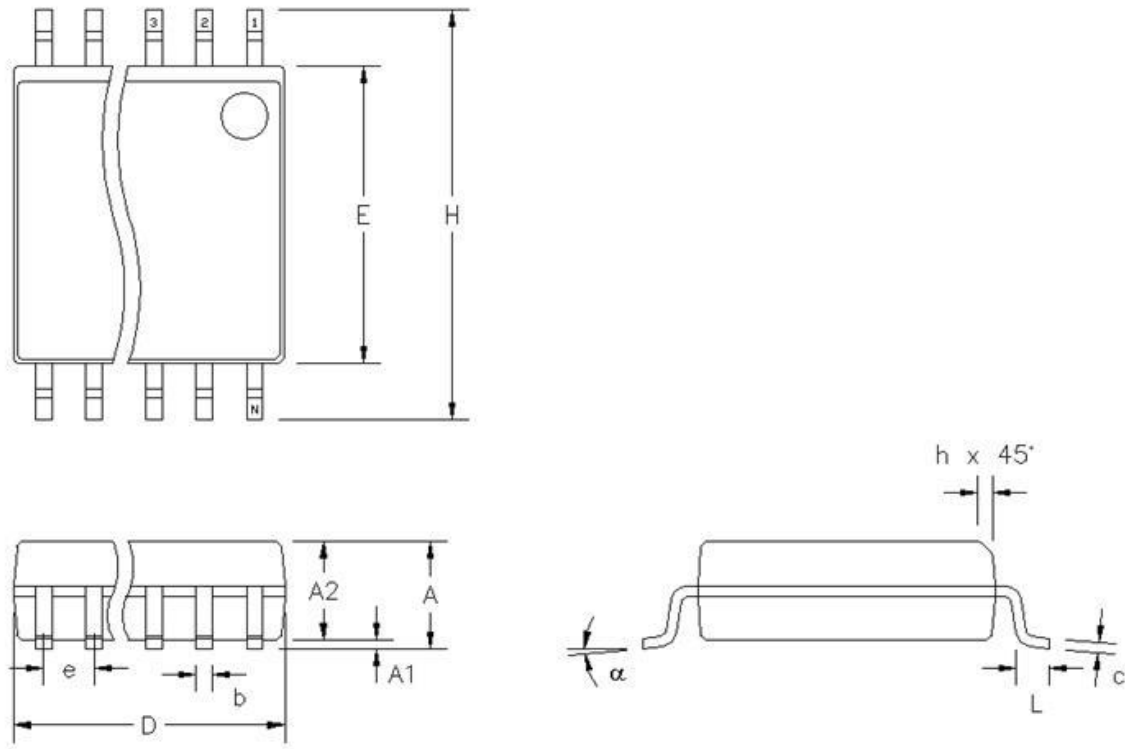


Figure 7 : SOIC16 Package Dimensions [inches]

[mm]	A	A1	A2	D	E	H	L	b	c	e	h	α
min	2.44	0.10	2.24	10.11	7.40	10.11	0.51	0.35	0.23	1.27	0.25	0°
max	2.64	0.30	2.44	10.46	7.60	10.51	1.02	0.48	0.32	BSC	0.71	8°

[inch]	A	A1	A2	D	E	H	L	b	c	e	h	α
min	.096	.004	.088	.398	.291	.398	.020	.014	.009	.050	.010	0°
max	.104	.012	.096	.412	.299	.414	.040	.019	.013	BSC	.028	8°

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